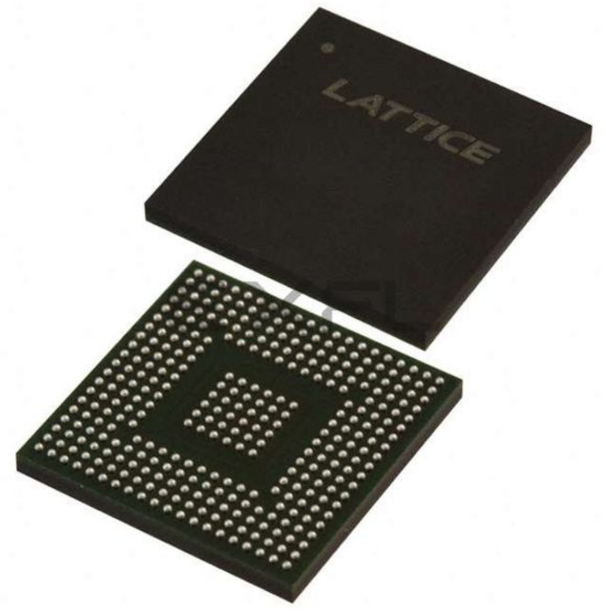
Lattice Semiconductor Corporation - LCMXO2-7000HE-5BG332C Datasheet



Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	858
Number of Logic Elements/Cells	6864
Total RAM Bits	245760
Number of I/O	278
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	332-FBGA
Supplier Device Package	332-CABGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo2-7000he-5bg332c

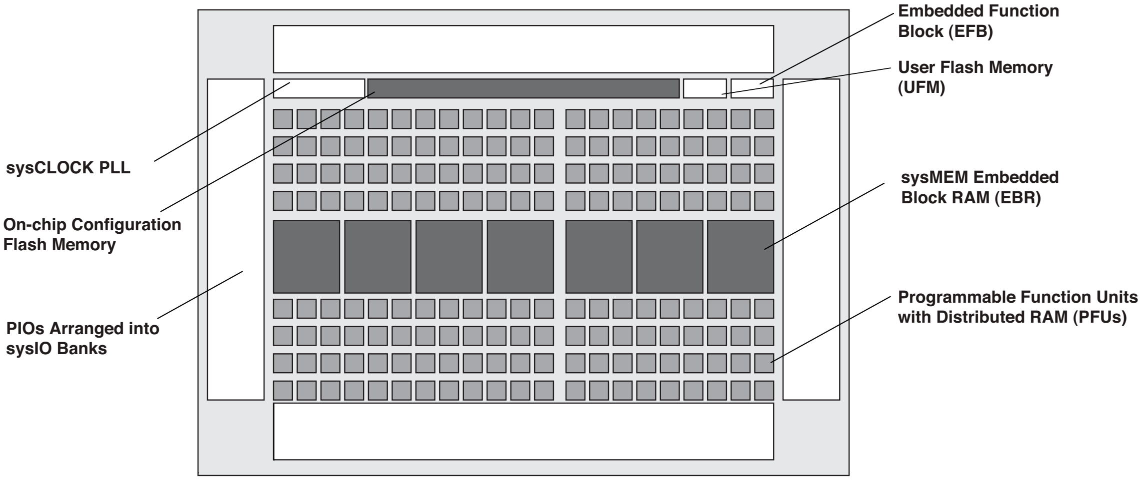
MachXO2 Family Data Sheet
Architecture

March 2016 **Data Sheet DS1035**

Architecture Overview

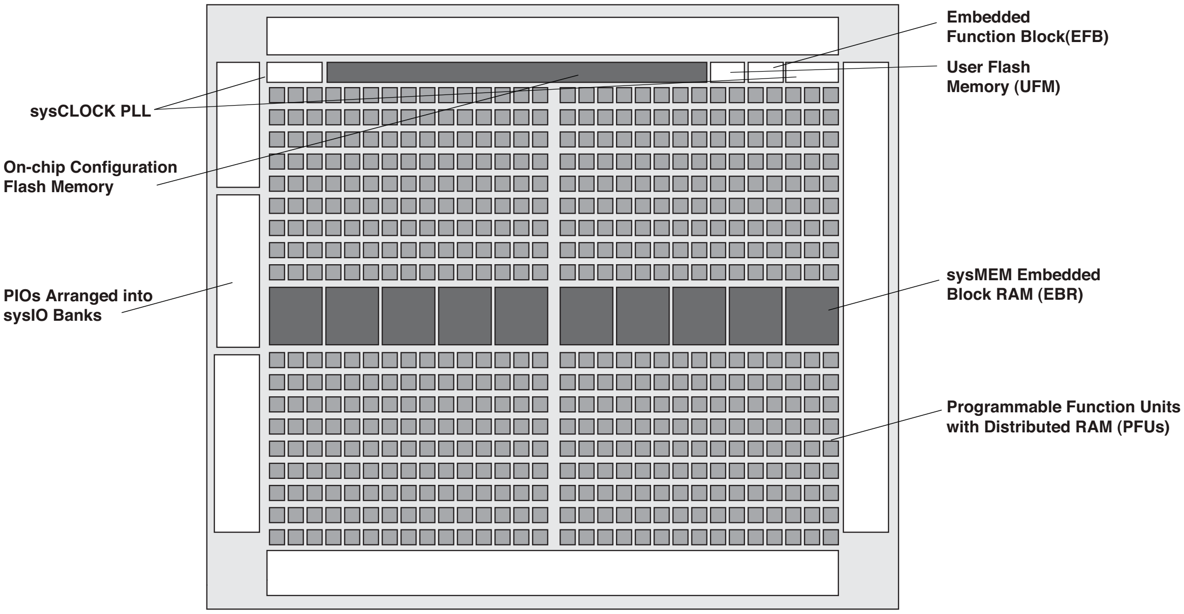
The MachXO2 family architecture contains an array of logic blocks surrounded by Programmable I/O (PIO). The larger logic density devices in this family have sysCLOCK™ PLLs and blocks of sysMEM Embedded Block RAM (EBRs). Figure 2-1 and Figure 2-2 show the block diagrams of the various family members.

Figure 2-1. Top View of the MachXO2-1200 Device



Note: MachXO2-256, and MachXO2-640/U are similar to MachXO2-1200. MachXO2-256 has a lower LUT count and no PLL or EBR blocks. MachXO2-640 has no PLL, a lower LUT count and two EBR blocks. MachXO2-640U has a lower LUT count, one PLL and seven EBR blocks.

Figure 2-2. Top View of the MachXO2-4000 Device



Note: MachXO2-1200U, MachXO2-2000/U and MachXO2-7000 are similar to MachXO2-4000. MachXO2-1200U and MachXO2-2000 have a lower LUT count, one PLL, and eight EBR blocks. MachXO2-2000U has a lower LUT count, two PLLs, and 10 EBR blocks. MachXO2-7000 has a higher LUT count, two PLLs, and 26 EBR blocks.

Modes of Operation

Each slice has up to four potential modes of operation: Logic, Ripple, RAM and ROM.

Logic Mode

In this mode, the LUTs in each slice are configured as 4-input combinatorial lookup tables. A LUT4 can have 16 possible input combinations. Any four input logic functions can be generated by programming this lookup table. Since there are two LUT4s per slice, a LUT5 can be constructed within one slice. Larger look-up tables such as LUT6, LUT7 and LUT8 can be constructed by concatenating other slices. Note LUT8 requires more than four slices.

Ripple Mode

Ripple mode supports the efficient implementation of small arithmetic functions. In Ripple mode, the following functions can be implemented by each slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Up/down counter with asynchronous clear
- Up/down counter with preload (sync)
- Ripple mode multiplier building block
- Multiplier support
- Comparator functions of A and B inputs
  - A greater-than-or-equal-to B
  - A not-equal-to B
  - A less-than-or-equal-to B

Ripple mode includes an optional configuration that performs arithmetic using fast carry chain methods. In this configuration (also referred to as CCU2 mode) two additional signals, Carry Generate and Carry Propagate, are generated on a per-slice basis to allow fast arithmetic functions to be constructed by concatenating slices.

RAM Mode

In this mode, a 16x4-bit distributed single port RAM (SPR) can be constructed by using each LUT block in Slice 0 and Slice 1 as a 16x1-bit memory. Slice 2 is used to provide memory address and control signals.

MachXO2 devices support distributed memory initialization.

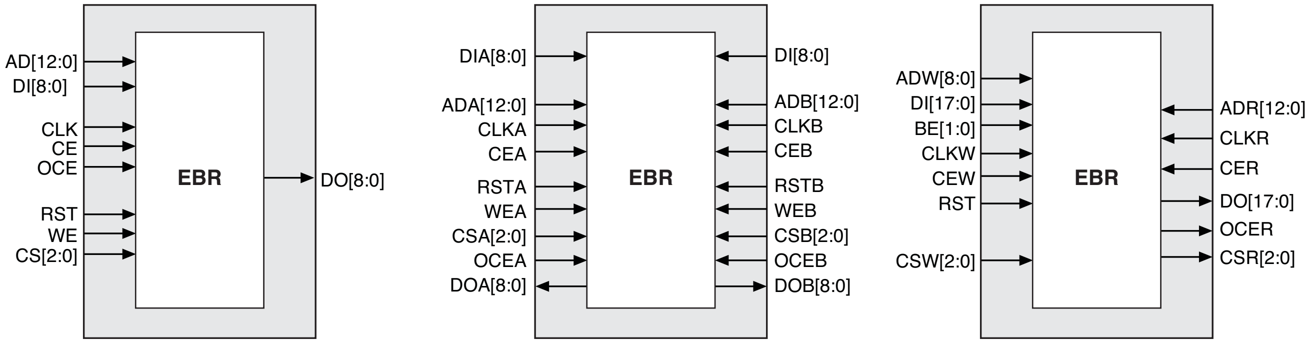
The Lattice design tools support the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. Table 2-3 shows the number of slices required to implement different distributed RAM primitives. For more information about using RAM in MachXO2 devices, please see TN1201, Memory Usage Guide for MachXO2 Devices.

Table 2-3. Number of Slices Required For Implementing Distributed RAM

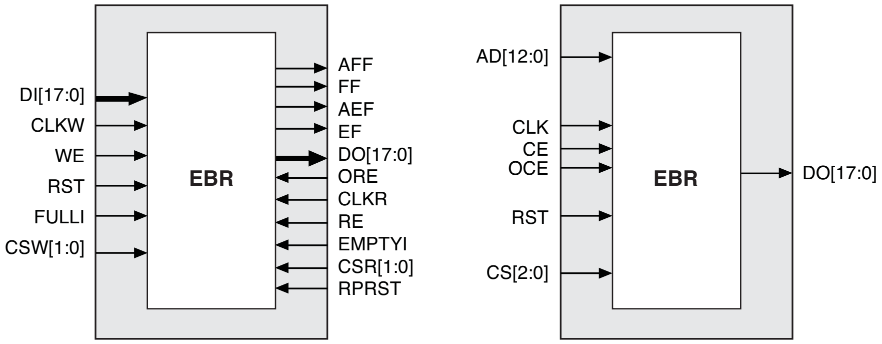
	SPR 16x4	PDPR 16x4
Number of slices	3	3

Note: SPR = Single Port RAM, PDPR = Pseudo Dual Port RAM

Figure 2-8. sysMEM Memory Primitives



Single-Port RAM **True Dual Port RAM** **Pseudo Dual Port RAM**



FIFO RAM **ROM**

Table 2-6. EBR Signal Descriptions

Port Name	Description	Active State
CLK	Clock	Rising Clock Edge
CE	Clock Enable	Active High
OCE[1]	Output Clock Enable	Active High
RST	Reset	Active High
BE[1]	Byte Enable	Active High
WE	Write Enable	Active High
AD	Address Bus	—
DI	Data In	—
DO	Data Out	—
CS	Chip Select	Active High
AFF	FIFO RAM Almost Full Flag	—
FF	FIFO RAM Full Flag	—
AEF	FIFO RAM Almost Empty Flag	—
EF	FIFO RAM Empty Flag	—
RPRST	FIFO RAM Read Pointer Reset	—

1. Optional signals.
2. For dual port EBR primitives a trailing ‘A’ or ‘B’ in the signal name specifies the EBR port A or port B respectively.
3. For FIFO RAM mode primitive, a trailing ‘R’ or ‘W’ in the signal name specifies the FIFO read port or write port respectively.
4. For FIFO RAM mode primitive FULLI has the same function as CSW(2) and EMPTYI has the same function as CSR(2).
5. In FIFO mode, CLKW is the write port clock, CSW is the write port chip select, CLKR is the read port clock, CSR is the read port chip select, ORE is the output read enable.

The EBR memory supports three forms of write behavior for single or dual port operation:

1. **Normal** – Data on the output appears only during the read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.

2. **Write Through** – A copy of the input data appears at the output of the same port. This mode is supported for all data widths.

3. **Read-Before-Write** – When new data is being written, the old contents of the address appears at the output.

FIFO Configuration

The FIFO has a write port with data-in, CEW, WE and CLKW signals. There is a separate read port with data-out, RCE, RE and CLKR signals. The FIFO internally generates Almost Full, Full, Almost Empty and Empty Flags. The Full and Almost Full flags are registered with CLKW. The Empty and Almost Empty flags are registered with CLKR. Table 2-7 shows the range of programming values for these flags.

Table 2-7. Programmable FIFO Flag Ranges

Flag Name	Programming Range
Full (FF)	1 to max (up to 2^N-1)
Almost Full (AF)	1 to Full-1
Almost Empty (AE)	1 to Full-1
Empty (EF)	0

N = Address bit width.

The FIFO state machine supports two types of reset signals: RST and RPRST. The RST signal is a global reset that clears the contents of the FIFO by resetting the read/write pointer and puts the FIFO flags in their initial reset state. The RPRST signal is used to reset the read pointer. The purpose of this reset is to retransmit the data that is in the FIFO. In these applications it is important to keep careful track of when a packet is written into or read from the FIFO.

Memory Core Reset

The memory core contains data output latches for ports A and B. These are simple latches that can be reset synchronously or asynchronously. RSTA and RSTB are local signals, which reset the output latches associated with port A and port B respectively. The Global Reset (GSRN) signal resets both ports. The output data latches and associated resets for both ports are as shown in Figure 2-9.

PIO

The PIO contains three blocks: an input register block, output register block and tri-state register block. These blocks contain registers for operating in a variety of modes along with the necessary clock and selection logic.

Table 2-8. PIO Signal List

Pin Name	I/O Type	Description
CE	Input	Clock Enable
D	Input	Pin input from sysIO buffer.
INDD	Output	Register bypassed input.
INCK	Output	Clock input
Q0	Output	DDR positive edge input
Q1	Output	Registered input/DDR negative edge input
D0	Input	Output signal from the core (SDR and DDR)
D1	Input	Output signal from the core (DDR)
TD	Input	Tri-state signal from the core
Q	Output	Data output signals to sysIO Buffer
TQ	Output	Tri-state output signals to sysIO Buffer
DQSR90[1]	Input	DQS shift 90-degree read clock
DQSW90[1]	Input	DQS shift 90-degree write clock
DDRCLKPOL[1]	Input	DDR input register polarity control signal from DQS
SCLK	Input	System clock for input and output/tri-state blocks.
RST	Input	Local set reset signal

1. Available in PIO on right edge only.

Input Register Block

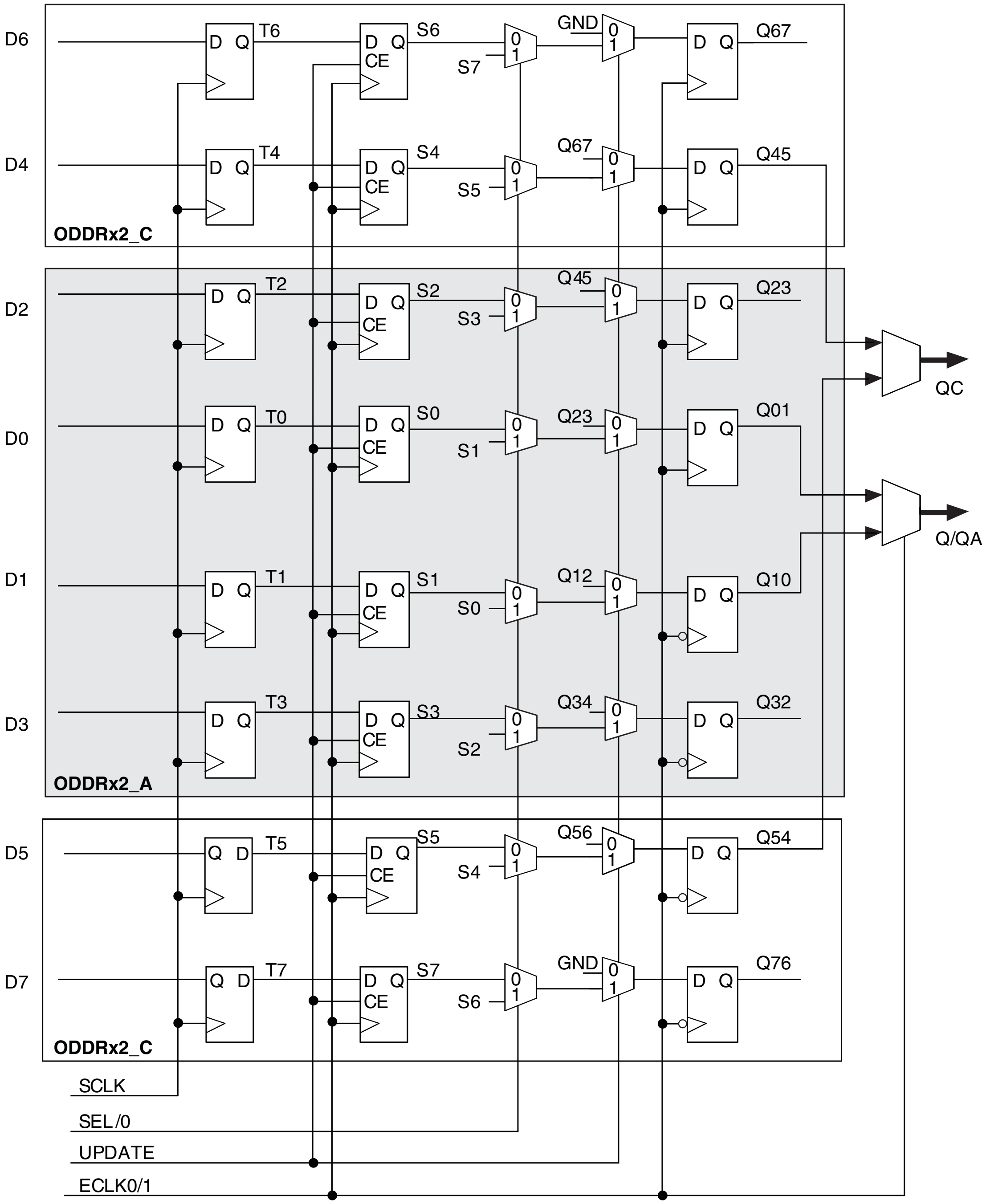
The input register blocks for the PIOs on all edges contain delay elements and registers that can be used to condition high-speed interface signals before they are passed to the device core. In addition to this functionality, the input register blocks for the PIOs on the right edge include built-in logic to interface to DDR memory.

Figure 2-12 shows the input register block for the PIOs located on the left, top and bottom edges. Figure 2-13 shows the input register block for the PIOs on the right edge.

Left, Top, Bottom Edges

Input signals are fed from the sysIO buffer to the input register block (as signal D). If desired, the input signal can bypass the register and delay elements and be used directly as a combinatorial signal (INDD), and a clock (INCK). If an input delay is desired, users can select a fixed delay. I/Os on the bottom edge also have a dynamic delay, DEL[4:0]. The delay, if selected, reduces input register hold time requirements when using a global clock. The input block allows two modes of operation. In single data rate (SDR) the data is registered with the system clock (SCLK) by one of the registers in the single data rate sync register block. In Generic DDR mode, two registers are used to sample the data on the positive and negative edges of the system clock (SCLK) signal, creating two data streams.

Figure 2-17. Output Gearbox



More information on the output gearbox is available in TN1203, Implementing High-Speed Interfaces with MachXO2 Devices.

DDR Memory Support

Certain PICs on the right edge of MachXO2-640U, MachXO2-1200/U and larger devices, have additional circuitry to allow the implementation of DDR memory interfaces. There are two groups of 14 or 12 PIOs each on the right edge with additional circuitry to implement DDR memory interfaces. This capability allows the implementation of up to 16-bit wide memory interfaces. One PIO from each group contains a control element, the DQS Read/Write Block, to facilitate the generation of clock and control signals (DQSR90, DQSW90, DDRCLKPOL and DATAVALID). These clock and control signals are distributed to the other PIO in the group through dedicated low skew routing.

DQS Read Write Block

Source synchronous interfaces generally require the input clock to be adjusted in order to correctly capture data at the input register. For most interfaces a PLL is used for this adjustment. However, in DDR memories the clock (referred to as DQS) is not free-running so this approach cannot be used. The DQS Read Write block provides the required clock alignment for DDR memory interfaces. DQSR90 and DQSW90 signals are generated by the DQS Read Write block from the DQS input.

In a typical DDR memory interface design, the phase relationship between the incoming delayed DQS strobe and the internal system clock (during the read cycle) is unknown. The MachXO2 family contains dedicated circuits to transfer data between these domains. To prevent set-up and hold violations, at the domain transfer between DQS (delayed) and the system clock, a clock polarity selector is used. This circuit changes the edge on which the data is registered in the synchronizing registers in the input register block. This requires evaluation at the start of each read cycle for the correct clock polarity. Prior to the read operation in DDR memories, DQS is in tri-state (pulled by termination). The DDR memory device drives DQS low at the start of the preamble state. A dedicated circuit in the DQS Read Write block detects the first DQS rising edge after the preamble state and generates the DDRCLKPOL signal. This signal is used to control the polarity of the clock to the synchronizing registers.

The temperature, voltage and process variations of the DQS delay block are compensated by a set of calibration signals (6-bit bus) from a DLL on the right edge of the device. The DLL loop is compensated for temperature, voltage and process variations by the system clock and feedback loop.

sysIO Buffer

Each I/O is associated with a flexible buffer referred to as a sysIO buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysIO buffers allow users to implement a wide variety of standards that are found in today's systems including LVCMOS, TTL, PCI, SSTL, HSTL, LVDS, BLVDS, MLVDS and LVPECL.

Each bank is capable of supporting multiple I/O standards. In the MachXO2 devices, single-ended output buffers, ratioed input buffers (LVTTL, LVCMOS and PCI), differential (LVDS) and referenced input buffers (SSTL and HSTL) are powered using I/O supply voltage (V_{CCIO}). Each sysIO bank has its own V_{CCIO}. In addition, each bank has a voltage reference, V_{REF}, which allows the use of referenced input buffers independent of the bank V_{CCIO}.

MachXO2-256 and MachXO2-640 devices contain single-ended ratioed input buffers and single-ended output buffers with complementary outputs on all the I/O banks. Note that the single-ended input buffers on these devices do not contain PCI clamps. In addition to the single-ended I/O buffers these two devices also have differential and referenced input buffers on all I/Os. The I/Os are arranged in pairs, the two pads in the pair are described as "T" and "C", where the true pad is associated with the positive side of the differential input buffer and the comp (complementary) pad is associated with the negative side of the differential input buffer.

Figure 2-18. MachXO2-1200U, MachXO2-2000/U, MachXO2-4000 and MachXO2-7000 Banks

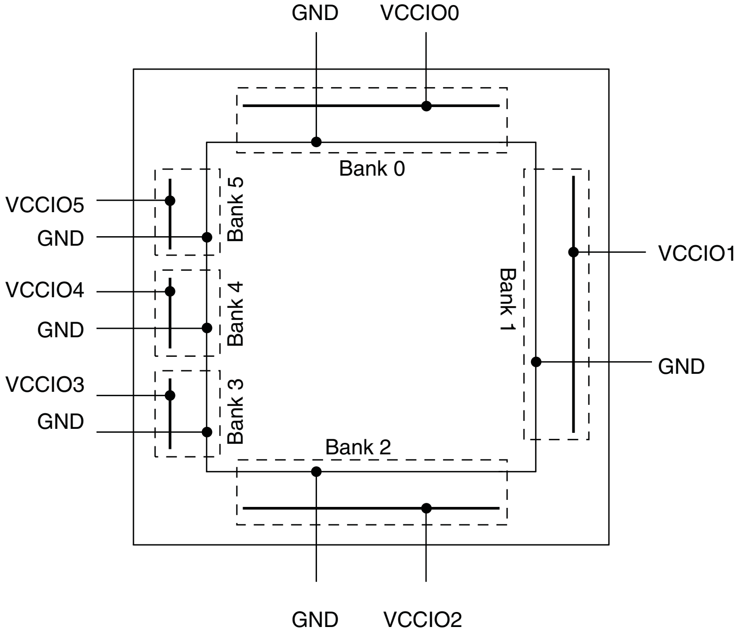
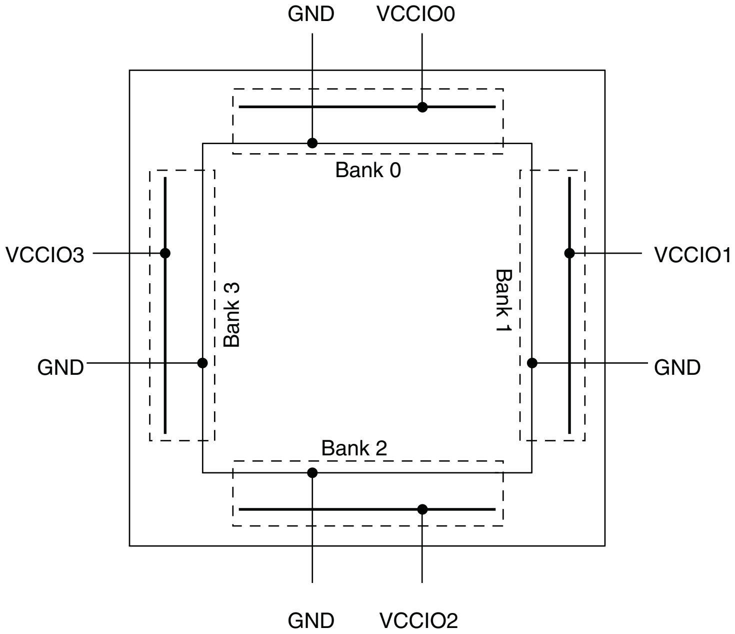


Figure 2-19. MachXO2-256, MachXO2-640/U and MachXO2-1200 Banks



DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
I_{IL}, I_{IH}[1, 4]	Input or I/O Leakage	Clamp OFF and $V_{CCIO} < V_{IN} < V_{IH}$ (MAX)	—	—	+175	µA
		Clamp OFF and $V_{IN} = V_{CCIO}$	–10	—	10	µA
		Clamp OFF and V_{CCIO} –0.97 V < V_{IN} < V_{CCIO}	–175	—	—	µA
		Clamp OFF and 0 V < V_{IN} < V_{CCIO} –0.97 V	—	—	10	µA
		Clamp OFF and V_{IN} = GND	—	—	10	µA
		Clamp ON and 0 V < V_{IN} < V_{CCIO}	—	—	10	µA
I_{PU}	I/O Active Pull-up Current	0 < V_{IN} < 0.7 V_{CCIO}	–30	—	-309	µA
I_{PD}	I/O Active Pull-down Current	V_{IL} (MAX) < V_{IN} < V_{CCIO}	30	—	305	µA
I_{BHLS}	Bus Hold Low sustaining current	$V_{IN} = V_{IL}$ (MAX)	30	—	—	µA
I_{BHHS}	Bus Hold High sustaining current	$V_{IN} = 0.7V_{CCIO}$	–30	—	—	µA
I_{BHLO}	Bus Hold Low Overdrive current	$0 \leq V_{IN} \leq V_{CCIO}$	—	—	305	µA
I_{BHHO}	Bus Hold High Overdrive current	$0 \leq V_{IN} \leq V_{CCIO}$	—	—	–309	µA
V_{BHT}[3]	Bus Hold Trip Points		V_{IL} (MAX)	—	V_{IH} (MIN)	V
C1	I/O Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	3	5	9	pF
C2	Dedicated Input Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	3	5.5	7	pF
V_{HYST}	Hysteresis for Schmitt Trigger Inputs[5]	V_{CCIO} = 3.3 V, Hysteresis = Large	—	450	—	mV
		V_{CCIO} = 2.5 V, Hysteresis = Large	—	250	—	mV
		V_{CCIO} = 1.8 V, Hysteresis = Large	—	125	—	mV
		V_{CCIO} = 1.5 V, Hysteresis = Large	—	100	—	mV
		V_{CCIO} = 3.3 V, Hysteresis = Small	—	250	—	mV
		V_{CCIO} = 2.5 V, Hysteresis = Small	—	150	—	mV
		V_{CCIO} = 1.8 V, Hysteresis = Small	—	60	—	mV
		V_{CCIO} = 1.5 V, Hysteresis = Small	—	40	—	mV

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. T_A 25 °C, f = 1.0 MHz.
3. Please refer to V_{IL} and V_{IH} in the sysIO Single-Ended DC Electrical Characteristics table of this document.
4. When V_{IH} is higher than V_{CCIO}, a transient current typically of 30 ns in duration or less with a peak current of 6 mA can occur on the high-to-low transition. For true LVDS output pins in MachXO2-640U, MachXO2-1200/U and larger devices, V_{IH} must be less than or equal to V_{CCIO}.
5. With bus keeper circuit turned on. For more details, refer to TN1202, MachXO2 sysIO Usage Guide.

Programming and Erase Flash Supply Current – ZE Devices[1, 2, 3, 4]

Symbol	Parameter	Device	Typ.[5]	Units
I_{CC}	Core Power Supply	LCMXO2-256ZE	13	mA
		LCMXO2-640ZE	14	mA
		LCMXO2-1200ZE	15	mA
		LCMXO2-2000ZE	17	mA
		LCMXO2-4000ZE	18	mA
		LCMXO2-7000ZE	20	mA
I_{CCIO}	Bank Power Supply[6]	All devices	0	mA

1. For further information on supply current, please refer to TN1198, Power Estimation and Management for MachXO2 Devices.
2. Assumes all inputs are held at V_{CCIO} or GND and all outputs are tri-stated.
3. Typical user pattern.
4. JTAG programming is at 25 MHz.
5. TJ = 25 °C, power supplies at nominal voltage.
6. Per bank. V_{CCIO} = 2.5 V. Does not include pull-up/pull-down.

Maximum sysIO Buffer Performance

I/O Standard	Max. Speed	Units
LVDS25	400	MHz
LVDS25E	150	MHz
RSDS25	150	MHz
RSDS25E	150	MHz
BLVDS25	150	MHz
BLVDS25E	150	MHz
MLVDS25	150	MHz
MLVDS25E	150	MHz
LVPECL33	150	MHz
LVPECL33E	150	MHz
SSTL25_I	150	MHz
SSTL25_II	150	MHz
SSTL25D_I	150	MHz
SSTL25D_II	150	MHz
SSTL18_I	150	MHz
SSTL18_II	150	MHz
SSTL18D_I	150	MHz
SSTL18D_II	150	MHz
HSTL18_I	150	MHz
HSTL18_II	150	MHz
HSTL18D_I	150	MHz
HSTL18D_II	150	MHz
PCI33	134	MHz
LVTTL33	150	MHz
LVTTL33D	150	MHz
LVCMOS33	150	MHz
LVCMOS33D	150	MHz
LVCMOS25	150	MHz
LVCMOS25D	150	MHz
LVCMOS25R33	150	MHz
LVCMOS18	150	MHz
LVCMOS18D	150	MHz
LVCMOS18R33	150	MHz
LVCMOS18R25	150	MHz
LVCMOS15	150	MHz
LVCMOS15D	150	MHz
LVCMOS15R33	150	MHz
LVCMOS15R25	150	MHz
LVCMOS12	91	MHz
LVCMOS12D	91	MHz

Parameter	Description	Device	–3		–2		–1		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Generic DDR4 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX4_RX.ECLK.Centered[9, 12]									
t_{SU}	Input Data Setup Before ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only[11]	0.434	—	0.535	—	0.630	—	ns
t_{HO}	Input Data Hold After ECLK		0.385	—	0.395	—	0.463	—	ns
f_{DATA}	DDRX4 Serial Input Data Speed		—	420	—	352	—	292	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency		—	210	—	176	—	146	MHz
f_{SCLK}	SCLK Frequency		—	53	—	44	—	37	MHz
7:1 LVDS Inputs – GDDR71_RX.ECLK.7.1[9, 12]									
t_{DVA}	Input Data Valid After ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only[11]	—	0.307	—	0.316	—	0.326	UI
t_{DVE}	Input Data Hold After ECLK		0.662	—	0.650	—	0.649	—	UI
f_{DATA}	DDR71 Serial Input Data Speed		—	420	—	352	—	292	Mbps
f_{DDR71}	DDR71 ECLK Frequency		—	210	—	176	—	146	MHz
f_{CLKIN}	7:1 Input Clock Frequency (SCLK) (minimum limited by PLL)		—	60	—	50	—	42	MHz
Generic DDR Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX1_TX.SCLK.Aligned[9, 12]									
t_{DIA}	Output Data Invalid After CLK Output	All MachXO2 devices, all sides	—	0.850	—	0.910	—	0.970	ns
t_{DIB}	Output Data Invalid Before CLK Output		—	0.850	—	0.910	—	0.970	ns
f_{DATA}	DDRX1 Output Data Speed		—	140	—	116	—	98	Mbps
f_{DDRX1}	DDRX1 SCLK frequency		—	70	—	58	—	49	MHz
Generic DDR Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX1_TX.SCLK.Centered[9, 12]									
t_{DVB}	Output Data Valid Before CLK Output	All MachXO2 devices, all sides	2.720	—	3.380	—	4.140	—	ns
t_{DVA}	Output Data Valid After CLK Output		2.720	—	3.380	—	4.140	—	ns
f_{DATA}	DDRX1 Output Data Speed		—	140	—	116	—	98	Mbps
f_{DDRX1}	DDRX1 SCLK Frequency (minimum limited by PLL)		—	70	—	58	—	49	MHz
Generic DDRX2 Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX2_TX.ECLK.Aligned[9, 12]									
t_{DIA}	Output Data Invalid After CLK Output	MachXO2-640U, MachXO2-1200/U and larger devices, top side only	—	0.270	—	0.300	—	0.330	ns
t_{DIB}	Output Data Invalid Before CLK Output		—	0.270	—	0.300	—	0.330	ns
f_{DATA}	DDRX2 Serial Output Data Speed		—	280	—	234	—	194	Mbps
f_{DDRX2}	DDRX2 ECLK frequency		—	140	—	117	—	97	MHz
f_{SCLK}	SCLK Frequency		—	70	—	59	—	49	MHz

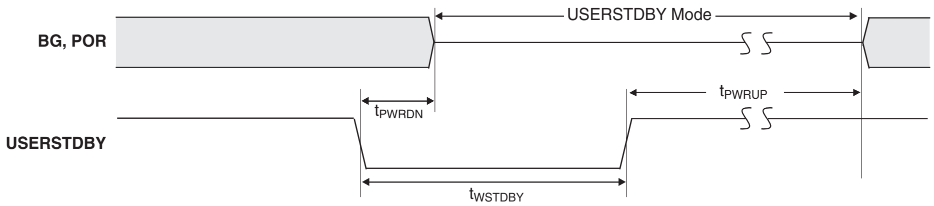
MachXO2 Oscillator Output Frequency

Symbol	Parameter	Min.	Typ.	Max	Units
f_{MAX}	Oscillator Output Frequency (Commercial Grade Devices, 0 to 85°C)	125.685	133	140.315	MHz
	Oscillator Output Frequency (Industrial Grade Devices, –40 °C to 100 °C)	124.355	133	141.645	MHz
t_{DT}	Output Clock Duty Cycle	43	50	57	%
t_{OPJIT}[1]	Output Clock Period Jitter	0.01	0.012	0.02	UIPP
$t_{STABLEOSC}$	STDBY Low to Oscillator Stable	0.01	0.05	0.1	µs

1. Output Clock Period Jitter specified at 133 MHz. The values for lower frequencies will be smaller UIPP. The typical value for 133 MHz is 95 ps and for 2.08 MHz the typical value is 1.54 ns.

MachXO2 Standby Mode Timing – HC/HE Devices

Symbol	Parameter	Device	Min.	Typ.	Max	Units
t_{PWRDN}	USERSTDBY High to Stop	All	—	—	9	ns
t_{PWRUP}	USERSTDBY Low to Power Up	LCMXO2-256		—		µs
		LCMXO2-640		—		µs
		LCMXO2-640U		—		µs
		LCMXO2-1200	20	—	50	µs
		LCMXO2-1200U		—		µs
		LCMXO2-2000		—		µs
		LCMXO2-2000U		—		µs
		LCMXO2-4000		—		µs
		LCMXO2-7000		—		µs
t_{WSTDBY}	USERSTDBY Pulse Width	All	18	—	—	ns



MachXO2 Standby Mode Timing – ZE Devices

Symbol	Parameter	Device	Min.	Typ.	Max	Units
t_{PWRDN}	USERSTDBY High to Stop	All	—	—	13	ns
t_{PWRUP}	USERSTDBY Low to Power Up	LCMXO2-256		—		µs
		LCMXO2-640		—		µs
		LCMXO2-1200	20	—	50	µs
		LCMXO2-2000		—		µs
		LCMXO2-4000		—		µs
		LCMXO2-7000		—		µs
t_{WSTDBY}	USERSTDBY Pulse Width	All	19	—	—	ns
$t_{BNDGAPSTBL}$	USERSTDBY High to Bandgap Stable	All	—	—	15	ns

	MachXO2-2000						MachXO2-2000U
	49 WLCSP	100 TQFP	132 csBGA	144 TQFP	256 caBGA	256 ftBGA	484 ftBGA
General Purpose I/O per Bank							
Bank 0	19	18	25	27	50	50	70
Bank 1	0	21	26	28	52	52	68
Bank 2	13	20	28	28	52	52	72
Bank 3	0	6	7	8	16	16	24
Bank 4	0	6	8	10	16	16	16
Bank 5	6	8	10	10	20	20	28
Total General Purpose Single-Ended I/O	38	79	104	111	206	206	278
Differential I/O per Bank							
Bank 0	7	9	13	14	25	25	35
Bank 1	0	10	13	14	26	26	34
Bank 2	6	10	14	14	26	26	36
Bank 3	0	3	3	4	8	8	12
Bank 4	0	3	4	5	8	8	8
Bank 5	3	4	5	5	10	10	14
Total General Purpose Differential I/O	16	39	52	56	103	103	139
Dual Function I/O	24	31	33	33	33	33	37
High-speed Differential I/O							
Bank 0	5	4	8	9	14	14	18
Gearboxes							
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	5	4	8	9	14	14	18
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	6	10	14	14	14	14	18
DQS Groups							
Bank 1	0	1	2	2	2	2	2
VCCIO Pins							
Bank 0	2	2	3	3	4	4	10
Bank 1	0	2	3	3	4	4	10
Bank 2	1	2	3	3	4	4	10
Bank 3	0	1	1	1	1	1	3
Bank 4	0	1	1	1	2	2	4
Bank 5	1	1	1	1	1	1	3
VCC	2	2	4	4	8	8	12
GND	4	8	10	12	24	24	48
NC	0	1	1	4	1	1	105
Reserved for Configuration	1	1	1	1	v	1	1
Total Count of Bonded Pins	39	100	132	144	256	256	484

Ultra Low Power Commercial Grade Devices, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-256ZE-1SG32C	256	1.2 V	–1	Halogen-Free QFN	32	COM
LCMXO2-256ZE-2SG32C	256	1.2 V	–2	Halogen-Free QFN	32	COM
LCMXO2-256ZE-3SG32C	256	1.2 V	–3	Halogen-Free QFN	32	COM
LCMXO2-256ZE-1UMG64C	256	1.2 V	–1	Halogen-Free ucBGA	64	COM
LCMXO2-256ZE-2UMG64C	256	1.2 V	–2	Halogen-Free ucBGA	64	COM
LCMXO2-256ZE-3UMG64C	256	1.2 V	–3	Halogen-Free ucBGA	64	COM
LCMXO2-256ZE-1TG100C	256	1.2 V	–1	Halogen-Free TQFP	100	COM
LCMXO2-256ZE-2TG100C	256	1.2 V	–2	Halogen-Free TQFP	100	COM
LCMXO2-256ZE-3TG100C	256	1.2 V	–3	Halogen-Free TQFP	100	COM
LCMXO2-256ZE-1MG132C	256	1.2 V	–1	Halogen-Free csBGA	132	COM
LCMXO2-256ZE-2MG132C	256	1.2 V	–2	Halogen-Free csBGA	132	COM
LCMXO2-256ZE-3MG132C	256	1.2 V	–3	Halogen-Free csBGA	132	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-640ZE-1TG100C	640	1.2 V	–1	Halogen-Free TQFP	100	COM
LCMXO2-640ZE-2TG100C	640	1.2 V	–2	Halogen-Free TQFP	100	COM
LCMXO2-640ZE-3TG100C	640	1.2 V	–3	Halogen-Free TQFP	100	COM
LCMXO2-640ZE-1MG132C	640	1.2 V	–1	Halogen-Free csBGA	132	COM
LCMXO2-640ZE-2MG132C	640	1.2 V	–2	Halogen-Free csBGA	132	COM
LCMXO2-640ZE-3MG132C	640	1.2 V	–3	Halogen-Free csBGA	132	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200ZE-1SG32C	1280	1.2 V	–1	Halogen-Free QFN	32	COM
LCMXO2-1200ZE-2SG32C	1280	1.2 V	–2	Halogen-Free QFN	32	COM
LCMXO2-1200ZE-3SG32C	1280	1.2 V	–3	Halogen-Free QFN	32	COM
LCMXO2-1200ZE-1TG100C	1280	1.2 V	–1	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-2TG100C	1280	1.2 V	–2	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-3TG100C	1280	1.2 V	–3	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-1MG132C	1280	1.2 V	–1	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-2MG132C	1280	1.2 V	–2	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-3MG132C	1280	1.2 V	–3	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-1TG144C	1280	1.2 V	–1	Halogen-Free TQFP	144	COM
LCMXO2-1200ZE-2TG144C	1280	1.2 V	–2	Halogen-Free TQFP	144	COM
LCMXO2-1200ZE-3TG144C	1280	1.2 V	–3	Halogen-Free TQFP	144	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-7000ZE-1TG144C	6864	1.2 V	–1	Halogen-Free TQFP	144	COM
LCMXO2-7000ZE-2TG144C	6864	1.2 V	–2	Halogen-Free TQFP	144	COM
LCMXO2-7000ZE-3TG144C	6864	1.2 V	–3	Halogen-Free TQFP	144	COM
LCMXO2-7000ZE-1BG256C	6864	1.2 V	–1	Halogen-Free caBGA	256	COM
LCMXO2-7000ZE-2BG256C	6864	1.2 V	–2	Halogen-Free caBGA	256	COM
LCMXO2-7000ZE-3BG256C	6864	1.2 V	–3	Halogen-Free caBGA	256	COM
LCMXO2-7000ZE-1FTG256C	6864	1.2 V	–1	Halogen-Free ftBGA	256	COM
LCMXO2-7000ZE-2FTG256C	6864	1.2 V	–2	Halogen-Free ftBGA	256	COM
LCMXO2-7000ZE-3FTG256C	6864	1.2 V	–3	Halogen-Free ftBGA	256	COM
LCMXO2-7000ZE-1BG332C	6864	1.2 V	–1	Halogen-Free caBGA	332	COM
LCMXO2-7000ZE-2BG332C	6864	1.2 V	–2	Halogen-Free caBGA	332	COM
LCMXO2-7000ZE-3BG332C	6864	1.2 V	–3	Halogen-Free caBGA	332	COM
LCMXO2-7000ZE-1FG484C	6864	1.2 V	–1	Halogen-Free fpBGA	484	COM
LCMXO2-7000ZE-2FG484C	6864	1.2 V	–2	Halogen-Free fpBGA	484	COM
LCMXO2-7000ZE-3FG484C	6864	1.2 V	–3	Halogen-Free fpBGA	484	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200ZE-1TG100CR1[1]	1280	1.2 V	–1	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-2TG100CR1[1]	1280	1.2 V	–2	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-3TG100CR1[1]	1280	1.2 V	–3	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-1MG132CR1[1]	1280	1.2 V	–1	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-2MG132CR1[1]	1280	1.2 V	–2	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-3MG132CR1[1]	1280	1.2 V	–3	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-1TG144CR1[1]	1280	1.2 V	–1	Halogen-Free TQFP	144	COM
LCMXO2-1200ZE-2TG144CR1[1]	1280	1.2 V	–2	Halogen-Free TQFP	144	COM
LCMXO2-1200ZE-3TG144CR1[1]	1280	1.2 V	–3	Halogen-Free TQFP	144	COM

1. Specifications for the “LCMXO2-1200ZE-speed package CR1” are the same as the “LCMXO2-1200ZE-speed package C” devices respectively, except as specified in the R1 Device Specifications section of this data sheet.

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-4000ZE-1QN84I	4320	1.2 V	–1	Halogen-Free QFN	84	IND
LCMXO2-4000ZE-2QN84I	4320	1.2 V	–2	Halogen-Free QFN	84	IND
LCMXO2-4000ZE-3QN84I	4320	1.2 V	–3	Halogen-Free QFN	84	IND
LCMXO2-4000ZE-1MG132I	4320	1.2 V	–1	Halogen-Free csBGA	132	IND
LCMXO2-4000ZE-2MG132I	4320	1.2 V	–2	Halogen-Free csBGA	132	IND
LCMXO2-4000ZE-3MG132I	4320	1.2 V	–3	Halogen-Free csBGA	132	IND
LCMXO2-4000ZE-1TG144I	4320	1.2 V	–1	Halogen-Free TQFP	144	IND
LCMXO2-4000ZE-2TG144I	4320	1.2 V	–2	Halogen-Free TQFP	144	IND
LCMXO2-4000ZE-3TG144I	4320	1.2 V	–3	Halogen-Free TQFP	144	IND
LCMXO2-4000ZE-1BG256I	4320	1.2 V	–1	Halogen-Free caBGA	256	IND
LCMXO2-4000ZE-2BG256I	4320	1.2 V	–2	Halogen-Free caBGA	256	IND
LCMXO2-4000ZE-3BG256I	4320	1.2 V	–3	Halogen-Free caBGA	256	IND
LCMXO2-4000ZE-1FTG256I	4320	1.2 V	–1	Halogen-Free ftBGA	256	IND
LCMXO2-4000ZE-2FTG256I	4320	1.2 V	–2	Halogen-Free ftBGA	256	IND
LCMXO2-4000ZE-3FTG256I	4320	1.2 V	–3	Halogen-Free ftBGA	256	IND
LCMXO2-4000ZE-1BG332I	4320	1.2 V	–1	Halogen-Free caBGA	332	IND
LCMXO2-4000ZE-2BG332I	4320	1.2 V	–2	Halogen-Free caBGA	332	IND
LCMXO2-4000ZE-3BG332I	4320	1.2 V	–3	Halogen-Free caBGA	332	IND
LCMXO2-4000ZE-1FG484I	4320	1.2 V	–1	Halogen-Free fpBGA	484	IND
LCMXO2-4000ZE-2FG484I	4320	1.2 V	–2	Halogen-Free fpBGA	484	IND
LCMXO2-4000ZE-3FG484I	4320	1.2 V	–3	Halogen-Free fpBGA	484	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-7000ZE-1TG144I	6864	1.2 V	–1	Halogen-Free TQFP	144	IND
LCMXO2-7000ZE-2TG144I	6864	1.2 V	–2	Halogen-Free TQFP	144	IND
LCMXO2-7000ZE-3TG144I	6864	1.2 V	–3	Halogen-Free TQFP	144	IND
LCMXO2-7000ZE-1BG256I	6864	1.2 V	–1	Halogen-Free caBGA	256	IND
LCMXO2-7000ZE-2BG256I	6864	1.2 V	–2	Halogen-Free caBGA	256	IND
LCMXO2-7000ZE-3BG256I	6864	1.2 V	–3	Halogen-Free caBGA	256	IND
LCMXO2-7000ZE-1FTG256I	6864	1.2 V	–1	Halogen-Free ftBGA	256	IND
LCMXO2-7000ZE-2FTG256I	6864	1.2 V	–2	Halogen-Free ftBGA	256	IND
LCMXO2-7000ZE-3FTG256I	6864	1.2 V	–3	Halogen-Free ftBGA	256	IND
LCMXO2-7000ZE-1BG332I	6864	1.2 V	–1	Halogen-Free caBGA	332	IND
LCMXO2-7000ZE-2BG332I	6864	1.2 V	–2	Halogen-Free caBGA	332	IND
LCMXO2-7000ZE-3BG332I	6864	1.2 V	–3	Halogen-Free caBGA	332	IND
LCMXO2-7000ZE-1FG484I	6864	1.2 V	–1	Halogen-Free fpBGA	484	IND
LCMXO2-7000ZE-2FG484I	6864	1.2 V	–2	Halogen-Free fpBGA	484	IND
LCMXO2-7000ZE-3FG484I	6864	1.2 V	–3	Halogen-Free fpBGA	484	IND

High Performance Industrial Grade Devices Without Voltage Regulator, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000HE-4TG100I	2112	1.2 V	–4	Halogen-Free TQFP	100	IND
LCMXO2-2000HE-5TG100I	2112	1.2 V	–5	Halogen-Free TQFP	100	IND
LCMXO2-2000HE-6TG100I	2112	1.2 V	–6	Halogen-Free TQFP	100	IND
LCMXO2-2000HE-4MG132I	2112	1.2 V	–4	Halogen-Free csBGA	132	IND
LCMXO2-2000HE-5MG132I	2112	1.2 V	–5	Halogen-Free csBGA	132	IND
LCMXO2-2000HE-6MG132I	2112	1.2 V	–6	Halogen-Free csBGA	132	IND
LCMXO2-2000HE-4TG144I	2112	1.2 V	–4	Halogen-Free TQFP	144	IND
LCMXO2-2000HE-5TG144I	2112	1.2 V	–5	Halogen-Free TQFP	144	IND
LCMXO2-2000HE-6TG144I	2112	1.2 V	–6	Halogen-Free TQFP	144	IND
LCMXO2-2000HE-4BG256I	2112	1.2 V	–4	Halogen-Free caBGA	256	IND
LCMXO2-2000HE-5BG256I	2112	1.2 V	–5	Halogen-Free caBGA	256	IND
LCMXO2-2000HE-6BG256I	2112	1.2 V	–6	Halogen-Free caBGA	256	IND
LCMXO2-2000HE-4FTG256I	2112	1.2 V	–4	Halogen-Free ftBGA	256	IND
LCMXO2-2000HE-5FTG256I	2112	1.2 V	–5	Halogen-Free ftBGA	256	IND
LCMXO2-2000HE-6FTG256I	2112	1.2 V	–6	Halogen-Free ftBGA	256	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000UHE-4FG484I	2112	1.2 V	–4	Halogen-Free fpBGA	484	IND
LCMXO2-2000UHE-5FG484I	2112	1.2 V	–5	Halogen-Free fpBGA	484	IND
LCMXO2-2000UHE-6FG484I	2112	1.2 V	–6	Halogen-Free fpBGA	484	IND

MachXO2 Family Data Sheet Revision History

March 2017 **Data Sheet DS1035**

Date	Version	Section	Change Summary
March 2017	3.3	DC and Switching Characteristics	Updated the Absolute Maximum Ratings section. Added standards.
			Updated the sysIO Recommended Operating Conditions section. Added standards.
			Updated the sysIO Single-Ended DC Electrical Characteristics section. Added standards.
			Updated the MachXO2 External Switching Characteristics – HC/HE Devices section. Under 7:1 LVDS Outputs – GDDR71_TX.ECLK.7:1, the D_{VB} and the D_{VA} parameters were changed to D_{IB} and $D_{IA.}$ The parameter descriptions were also modified.
			Updated the MachXO2 External Switching Characteristics – ZE Devices section. Under 7:1 LVDS Outputs – GDDR71_TX.ECLK.7:1, the D_{VB} and the D_{VA} parameters were changed to D_{IB} and $D_{IA.}$ The parameter descriptions were also modified.
			Updated the sysCONFIG Port Timing Specifications section. Corrected the t_{INITL} units from ns to µs.
		Pinout Information	Updated the Signal Descriptions section. Revised the descriptions of the PROGRAMN, INITN, and DONE signals.
			Updated the Pinout Information Summary section. Added footnote to MachXO2-1200 32 QFN.
		Ordering Information	Updated the MachXO2 Part Number Description section. Corrected the MG184, BG256, FTG256 package information. Added “(0.8 mm Pitch)” to BG332.
			Updated the Ultra Low Power Industrial Grade Devices, Halogen Free (RoHS) Packaging section. — Updated LCMXO2-1200ZE-1UWG25ITR50 footnote. — Corrected footnote numbering typo. — Added the LCMXO2-2000ZE-1UWG49ITR50 and LCMXO2-2000ZE-1UWG49ITR1K part numbers. Updated/added footnote/s.

Date	Version	Section	Change Summary
May 2011	01.3	Multiple	Replaced "SED" with "SRAM CRC Error Detection" throughout the document.
		DC and Switching Characteristics	Added footnote 1 to Program Erase Specifications table.
		Pinout Information	Updated Pin Information Summary tables.
			Signal name SO/SISPISO changed to SO/SPISO in the Signal Descriptions table.
April 2011	01.2	—	Data sheet status changed from Advance to Preliminary.
		Introduction	Updated MachXO2 Family Selection Guide table.
		Architecture	Updated Supported Input Standards table.
			Updated sysMEM Memory Primitives diagram.
			Added differential SSTL and HSTL IO standards.
		DC and Switching Characteristics	Updates following parameters: POR voltage levels, DC electrical characteristics, static supply current for ZE/HE/HC devices, static power consumption contribution of different components – ZE devices, programming and erase Flash supply current.
			Added VREF specifications to sysIO recommended operating conditions.
			Updating timing information based on characterization.
			Added differential SSTL and HSTL IO standards.
		Ordering Information	Added Ordering Part Numbers for R1 devices, and devices in WLCSP packages.
			Added R1 device specifications.
January 2011	01.1	All	Included ultra-high I/O devices.
		DC and Switching Characteristics	Recommended Operating Conditions table – Added footnote 3.
			DC Electrical Characteristics table – Updated data for I_{IL}, I_{IH}. V_{HYST} typical values updated.
			Generic DDRX2 Outputs with Clock and Data Aligned at Pin (GDDRX2_TX.ECLK.Aligned) Using PCLK Pin for Clock Input tables – Updated data for T_{DIA} and $T_{DIB.}$
			Generic DDRX4 Outputs with Clock and Data Aligned at Pin (GDDRX4_TX.ECLK.Aligned) Using PCLK Pin for Clock Input tables – Updated data for T_{DIA} and $T_{DIB.}$
			Power-On-Reset Voltage Levels table - clarified note 3.
			Clarified VCCIO related recommended operating conditions specifications.
			Added power supply ramp rate requirements.
			Added Power Supply Ramp Rates table.
			Updated Programming/Erase Specifications table.
			Removed references to $V_{CCP.}$
		Pinout Information	Included number of 7:1 and 8:1 gearboxes (input and output) in the pin information summary tables.
			Removed references to $V_{CCP.}$
November 2010	01.0	—	Initial release.